

Amendments to the Claims:

This listing of the claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (withdrawn) A method of making electro-mechanical circuit elements comprising the acts of:
providing a structure having electrically conductive traces and supports, the supports extending from a surface of the substrate;
providing a layer of nanotubes over the supports; and
selectively removing portions of the layer of nanotubes to form ribbons of nanotubes that cross the electrically conductive traces, wherein each ribbon comprises one or more nanotubes.
2. (withdrawn) The method of claim 1 wherein the act of providing a structure provides a structure in which the electrically conductive traces are doped silicon traces.
3. (withdrawn) The method of claim 1 wherein the act of providing a structure provides a structure in which the electrically conductive traces are nanotubes.
4. (withdrawn) The method of claim 1 wherein the act of providing a structure provides a structure in which the electrically conductive traces are ribbons of nanotubes.
5. (withdrawn) The method of claim 1 wherein the act of providing a structure provides a structure in which the support structures are formed as rows of material and wherein the electrically conductive traces are substantially parallel to the rows.
6. (withdrawn) The method of claim 5 wherein the traces are separated from the supports.
7. (withdrawn) The method of claim 5 wherein the traces contact the supports.

8. (withdrawn) The method of claim 1 wherein the traces are separated from the supports.
9. (withdrawn) The method of claim 1 wherein the traces contact the supports.
10. (withdrawn) The method of claim 1 wherein the act of providing a structure provides a structure in which the supports are made from silicon nitride.
11. (withdrawn) The method of claim 1 wherein the act of providing a structure provides a structure in which the electrically conductive traces are over a layer of insulating material to electrically isolate the traces relative to one another.
12. (withdrawn) The method of claim 1 wherein the act of providing a structure provides a structure in which the electrically conductive traces are each over insulating material to electrically isolate the traces.
13. (withdrawn) The method of claim 1 wherein the act of providing a layer of nanotubes provides a non-woven fabric of nanotubes.
14. (withdrawn) The method of claim 13 in which the fabric is grown on the structure.
15. (withdrawn) The method of claim 13 in which the structure includes a sacrificial layer of material over the traces and in which the fabric is grown over the sacrificial layer.
16. (withdrawn) The method of claim 14 in which the structure is treated with a catalyst to facilitate the growth of the fabric.
17. (withdrawn) The method of claim 15 in which an upper surface of the sacrificial layer is treated with a catalyst to facilitate the growth of the fabric.

18. (withdrawn) The method of claim 1 in which the act of selectively removing includes the act of patterning and etching the layer of nanotubes to form the ribbons.
19. (withdrawn) The method of claim 13 in which the act of selectively removing includes the act of patterning and etching the fabric of nanotubes to form the ribbons.
20. (withdrawn) The method of claim 14 wherein the growth of nanotubes is substantially unrestrained over the surface of the structure.
21. (withdrawn) The method of claim 18 wherein the act of patterning and etching uses etchants that diffuse through the fabric.
22. (withdrawn) The method of claim 1 wherein the layer of nanotubes is substantially a monolayer.
23. (currently amended) An electromechanical circuit, comprising:
a structure having electrically conductive traces and supports extending from a surface of
[[the]] a substrate; and
nanotube ribbons suspended by the supports that cross the electrically conductive traces,
~~wherein each ribbon comprises one or more nanotubes.~~
wherein each ribbon has a cross-sectional area that is substantially rectangular.
24. (original) The circuit of claim 23 wherein the electrically conductive traces are doped silicon traces.
25. (original) The circuit of claim 23 wherein the electrically conductive traces are nanotubes.
26. (original) The circuit of claim 23 wherein the electrically conductive traces are ribbons of nanotubes.

27. (original) The circuit of claim 23 wherein the supports are rows of material and wherein the traces are substantially parallel to the rows.
28. (original) The circuit of claim 27 wherein the traces are separated from the supports.
29. (original) The circuit of claim 27 wherein the traces contact the supports.
30. (original) The circuit of claim 23 wherein the supports are made from silicon nitride.
31. (original) The circuit of claim 23 wherein the electrically conductive traces are over a layer of insulating material to electrically isolate the traces relative to one another.
32. (original) The circuit of claim 23 wherein the electrically conductive traces are each over insulating material to electrically isolate the traces.
33. (currently amended) The circuit of claim 23 wherein ribbons are of a non-woven fabric of ~~nanotubes~~ nanotubes.
34. (original) The circuit of claim 23 wherein the ribbons are substantially a monolayer of nanotubes.
35. (withdrawn) The method of claim 1 wherein the act of providing a layer of nanotubes includes applying nanotubes to the substrate.
36. (withdrawn) A method of making a circuit element comprising the acts of:
providing a structure having at least one electrically conductive trace in predefined orientation;
providing a layer of nanotubes; and

selectively removing portions of the layer of nanotubes to form a ribbon of nanotubes that crosses the electrically conductive trace but in a spaced relation thereto.

37. (withdrawn) The method of claim 36 wherein the structure includes supports and wherein the formation of the ribbon in spaced relation to the electrically conductive traces creates a ribbon that is suspended from the supports.

38. (withdrawn) The method of claim 36 in which the act of selectively removing includes the act of patterning and etching the layer of nanotubes to form the ribbon.

39. (withdrawn) A method of making a circuit element comprising the acts of:
providing a structure having at least one electrically conductive trace in predefined orientation;
providing a fabric of nanotubes; and
selectively removing portions of the layer of nanotubes according to a predefined pattern to form a ribbon having at least one nanotube such that the ribbon crosses the electrically conductive trace but in a spaced relation thereto.

40. (withdrawn) The method of claim 39 wherein the structure includes supports and wherein the formation of the ribbon in spaced relation to the electrically conductive traces creates a ribbon that is suspended from the supports.

41. (withdrawn) The method of claim 39 in which the act of selectively removing includes the act of patterning and etching the fabric of nanotubes to form the ribbon.

42. (withdrawn) A system, comprising:
a structure having an electrically conductive trace;
a nanotube ribbon having a plurality of nanotubes in electrical contact, the ribbon being disposed in spaced and crossed relation to the electrically conductive trace.

43. (withdrawn) A system, comprising:
a structure having an electrically conductive trace;
a nanotube ribbon having at least one nanotube, the ribbon being of predefined shape, and
disposed in spaced and crossed relation to the electrically conductive trace.
44. (new) An electromechanical circuit, comprising:
a structure having electrically conductive traces and supports extending from a surface of
a substrate; and
nanotube ribbons suspended by the supports that cross the electrically conductive traces,
wherein each ribbon is flat.
45. (new) The circuit of claim 44 wherein the electrically conductive traces are doped silicon
traces.
46. (new) The circuit of claim 44 wherein the electrically conductive traces are nanotubes.
47. (new) The circuit of claim 44 wherein the electrically conductive traces are ribbons of
nanotubes.
48. (new) The circuit of claim 44 wherein the supports are rows of material and wherein the
traces are substantially parallel to the rows.
49. (new) The circuit of claim 44 wherein the traces are separated from the supports.
50. (new) The circuit of claim 44 wherein the traces contact the supports.
51. (new) The circuit of claim 44 wherein the supports are made from silicon nitride.
52. (new) The circuit of claim 44 wherein the electrically conductive traces are over a layer
of insulating material to electrically isolate the traces relative to one another.

53. (new) The circuit of claim 44 wherein the electrically conductive traces are each over insulating material to electrically isolate the traces.

54. (new) The circuit of claim 44 wherein ribbons are of a non-woven fabric of nanotubes.

55. (new) The circuit of claim 44 wherein the ribbons are substantially a monolayer of nanotubes.

56. (new) An electromechanical circuit, comprising:
a structure having electrically conductive traces and supports extending from a surface of a substrate; and
nanotube ribbons suspended by the supports that cross the electrically conductive traces, wherein each ribbon comprises a plurality of nanotubes.

57. (new) The circuit of claim 56 wherein the electrically conductive traces are doped silicon traces.

58. (new) The circuit of claim 56 wherein the electrically conductive traces are nanotubes.

59. (new) The circuit of claim 56 wherein the electrically conductive traces are ribbons of nanotubes.

60. (new) The circuit of claim 56 wherein the supports are rows of material and wherein the traces are substantially parallel to the rows.

61. (new) The circuit of claim 56 wherein the traces are separated from the supports.

62. (new) The circuit of claim 56 wherein the traces contact the supports.

63. (new) The circuit of claim 56 wherein the supports are made from silicon nitride.
64. (new) The circuit of claim 56 wherein the electrically conductive traces are over a layer of insulating material to electrically isolate the traces relative to one another.
65. (new) The circuit of claim 56 wherein the electrically conductive traces are each over insulating material to electrically isolate the traces.
66. (new) The circuit of claim 56 wherein ribbons are of a non-woven fabric of nanotubes.
67. (new) The circuit of claim 56 wherein the ribbons are substantially a monolayer of nanotubes.